


SC2NXXX901 Series Product Portfolio

Generic Part Number	Semicoa Part Number	Transistor Description	Package	Type	V _{CEO} (V)	I _C (mA)	f _T (Min) (MHz)
2N2222AUB	SC2N2222AUB901	Switching	UB	NPN	50	800	250
2N2484UB	SC2N2484UB901	Low Power	UB	NPN	60	50	60
2N2857UB	SC2N2857UB901	Low Power, High Frequency	UB	NPN	15	40	1000
2N2907AUB	SC2N2907AUB901	Switching	UB	PNP	60	600	200
2N3501UB	SC2N3501UB901	Amplifier	UB	NPN	150	300	150
2N3700UB	SC2N3700UB901	Low Power	UB	NPN	80	1000	100
2N3866AUB	SC2N3866AUB901	High Frequency	UB	NPN	30	400	800
2N3904AUB	SC2N3904AUB901	Switching	UB	NPN	40	200	300
2N3906AUB	SC2N3906AUB901	Switching	UB	PNP	40	200	250
2N4033UB	SC2N4033UB901	Switching	UB	PNP	80	1000	150
2N4261UB	SC2N4261UB901	Switching, High Frequency	UB	PNP	15	30	2000
2N4957UB	SC2N4957UB901	Amplifier, High Frequency	UB	PNP	30	30	1200
2N5109UB	SC2N5109UB901	High Frequency	UB	NPN	20	400	1000

SC2N2907AUB901 

Low Cost, Low Power, Silicon PNP, Switching, Bipolar Transistor, Rad Tolerant, Surface Mount

DESCRIPTION
The SC2N2907AUB901 is a Low Cost, Low Power, Switching, Silicon PNP, Bipolar Transistor, in a Surface Mount package ideal for Commercial Space applications with minimal radiation requirements (100 krad, Low Dose Rate @ 100 mrad/s). Parts come from wafers that have gone through sample evaluation to demonstrate a high level of reliability and quality. Package parts are 100% tested for DC parameter per for moisture with a sample test for high and low temperature.


FEATURES

- Surface Mount
- Wafer pass sample evaluation prior to packaging for greater quality assurance.
- Radiation Tolerant to 30 krad (Low Dose Rate) with minimal parameter degradation.
- Laser Marked with part number: SC2907AUB901

Electrical Characteristics at T_a = 25 °C unless otherwise stated:

Parameter	Test Conditions	Minimum	Maximum	Units
V _{CEO}	V _{CE} = 50 V			V
V _{CE(sat)}	V _{CE} = 5 V			V
V _{CE(sat)}	I _C = 10 mA, I _B = 1 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 10 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 125 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 150 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 175 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 200 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 225 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 250 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 275 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 300 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 325 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 350 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 375 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 400 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 425 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 450 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 475 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 500 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 525 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 550 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 575 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 600 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 625 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 650 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 675 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 700 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 725 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 750 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 775 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 800 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 825 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 850 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 875 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 900 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 925 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 950 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 975 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 1000 °C			V

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SC2N2222AUB901 

Low Cost, Low Power, Silicon NPN, Switching, Bipolar Transistor, Radiation Tolerant, Surface Mount

DESCRIPTION
The SC2N2222AUB901 is a Low Cost, Low Power, Switching, Silicon NPN, Bipolar Transistor, in a Surface Mount package ideal for Commercial Space applications with minimal radiation requirements (100 krad, Low Dose Rate @ 100 mrad/s). Parts come from wafers that have gone through sample evaluation to demonstrate a high level of reliability and quality. Package parts are 100% tested for DC parameter per for moisture with a sample test for high and low temperature.

FEATURES

- Surface Mount, UB Package.
- Wafer pass sample evaluation prior to packaging for greater quality assurance.
- Radiation Tolerant to 30 krad (Low Dose Rate) with minimal parameter degradation.
- Laser Marked with part number: SC2222A901

Electrical Characteristics at T_a = 25 °C unless otherwise stated:

Parameter	Test Conditions	Minimum	Maximum	Units
V _{CEO}	V _{CE} = 75 V			V
V _{CE(sat)}	V _{CE} = 8 V			V
V _{CE(sat)}	I _C = 10 mA, I _B = 1 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 10 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 125 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 150 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 175 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 200 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 225 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 250 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 275 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 300 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 325 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 350 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 375 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 400 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 425 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 450 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 475 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 500 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 525 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 550 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 575 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 600 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 625 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 650 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 675 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 700 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 725 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 750 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 775 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 800 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 825 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 850 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 875 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 900 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 925 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 950 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 975 °C			V
V _{CE(sat)}	I _C = 10 mA, I _B = 100 mA, T _a = 1000 °C			V

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ASSEMBLY AND TEST FLOW

DIE PREP

Final Probe

Die Prep

ASSEMBLY

Die Attach, Wire Bond, and Lid Seal

Quality Inspection

TEST

Laser Mark

DC Electrical Test (100%)

Quality Inspection

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